Eduardo Alves

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

769 papers	11,737 citations	50 h-index	71 g-index
794 ext. papers	12,700 ext. citations	2.6 avg, IF	5.86 L-index

#	Paper	IF	Citations
769	Improvement of Mechanical Properties with Non-Equimolar CrNbTaVW High Entropy Alloy. *Crystals* , **2022**, 12, 219	2.3	1
768	Structural analysis of the ZnO/MgO superlattices on a-polar ZnO substrates grown by MBE. *Applied Surface Science*, **2022**, 587, 152830	6.7	
767	Tantalum-Titanium Oxynitride Thin Films Deposited by DC Reactive Magnetron Co-Sputtering: Mechanical, Optical, and Electrical Characterization. *Coatings*, **2022**, 12, 36	2.9	2
766	Ta2O5/SiO2 Multicomponent Dielectrics for Amorphous Oxide TFTs. *Electronic Materials*, **2021**, 2, 1-16	0.8	0
765	Eu3+ optical activation engineering in Al Ga1-N nanowires for red solid-state nano-emitters. *Applied Materials Today*, **2021**, 22, 100893	6.6	1
764	Unravelling the secrets of the resistance of GaN to strongly ionising radiation. *Communications Physics*, **2021**, 4,	5.4	15
763	Simulating the effect of Ar+ energy implantation on the strain propagation in AlGaN. *Journal Physics D: Applied Physics*, **2021**, 54, 245301	3	2
762	Self-powered proton detectors based on GaN core□shell p□ microwires. *Applied Physics Letters*, **2021**, 118, 193501	3.4	1
761	An insider view of the Portuguese ion beam laboratory. *European Physical Journal Plus*, **2021**, 136, 1	3.1	4
760	Use of a Timepix position-sensitive detector for Rutherford backscattering spectrometry with channeling. *Nuclear Instruments & Methods in Physics Research B*, **2021**, 499, 61-69	1.2	
759	Dependence of optical properties on composition of silicon carbonitride thin films deposited at low temperature by PECVD. *Journal of Non-Crystalline Solids*, **2021**, 551, 120434	3.9	2
758	Microwave transient reflection in annealed SnS thin films. *Materials Science in Semiconductor Processing*, **2021**, 121, 105302	4.3	1
757	The effects of mechanical alloying on the physical and thermal properties of CuCrFeTiV alloy. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2021**, 263, 114805	3.1	0
756	Ion beam analysis of Li-Sn alloys for fusion applications. *Nuclear Instruments & Methods in Physics Research B*, **2021**, 486, 55-62	1.2	
755	Deposition of Ti-Zr-O-N films by reactive magnetron sputtering of Zr target with Ti ribbons. *Surface and Coatings Technology*, **2021**, 409, 126737	4.4	0
754	Electrical, optical and photoconductive properties of Sn-doped indium sulfofluoride thin films. *Materials Science in Semiconductor Processing*, **2021**, 121, 105349	4.3	0
753	Crystal mosaicity determined by a novel layer deconvolution Williamson□Hall method. *CrystEngComm*, **2021**, 23, 2048-2062	3.3	3

752	Multiple reflection optimization package for X-ray diffraction. *CrystEngComm*, **2021**, 23, 3308-3318	3.3	2
751	Enhanced red emission from Eu-implanted ZnMgO layers and ZnO/ZnMgO quantum structures. *Applied Physics Letters*, **2021**, 119, 112101	3.4	1
750	Nonpolar short-period ZnO/MgO superlattices: Radiative excitons analysis. *Journal of Luminescence* , **2021**, 238, 118288	3.8	2
749	In-situ annealing transmission electron microscopy of plasmonic thin films composed of bimetallic Au□Ag nanoparticles dispersed in a TiO2 matrix. *Vacuum*, **2021**, 193, 110511	3.7	0
748	Nanostructured c-Si surfaces obtained by sequential ion implantation of C+ and Ti+: Tribophysical and structural characterization. *Nuclear Instruments & Methods in Physics Research B*, **2020**, 471, 69-75	1.2	
747	Stopping power of hydrogen in hafnium and the importance of relativistic 4f electrons. *Physical Review A*, **2020**, 101,	2.6	4
746	Post-mortem analysis of tungsten plasma facing components in tokamaks: Raman microscopy measurements on compact, porous oxide and nitride films and nanoparticles. *Nuclear Fusion*, **2020**, 60, 086004	3.3	3
745	Oxidation behaviour of neutron irradiated Be pebbles. *Nuclear Materials and Energy*, **2020**, 23, 100748	2.1	1
744	Fuel inventory and material migration of JET main chamber plasma facing components compared over three operational periods. *Physica Scripta*, **2020**, T171, 014051	2.6	11
743	Deposition in the tungsten divertor during the 2011□2016 campaigns in JET with ITER-like wall. *Physica Scripta*, **2020**, T171, 014044	2.6	6
742	Effect of composition and surface characteristics on fuel retention in beryllium-containing co-deposited layers. *Physica Scripta*, **2020**, T171, 014038	2.6	8
741	Ar+ ion irradiation of magnetic tunnel junction multilayers: impact on the magnetic and electrical properties. *Journal Physics D: Applied Physics*, **2020**, 53, 455003	3	2
740	W/AlSiTiNx/SiAlTiOyNx/SiAlOx multilayered solar thermal selective absorber coating. *Solar Energy*, **2020**, 207, 192-198	6.8	9
739	Study of structural and optical properties of MBE grown nonpolar (10-10) ZnO/ZnMgO photonic structures. *Optical Materials*, **2020**, 100, 109709	3.3	6
738	Nanocomposite Au-ZnO thin films: Influence of gold concentration and thermal annealing on the microstructure and plasmonic response. *Surface and Coatings Technology*, **2020**, 385, 125379	4.4	3
737	Advanced Monte Carlo Simulations for Ion-Channeling Studies of Complex Defects in Crystals. *Springer Series in Materials Science*, **2020**, 133-160	0.9	2
736	Photoelectrochemical Water Splitting: Thermal Annealing Challenges on Hematite Nanowires. *Journal of Physical Chemistry C*, **2020**, 124, 12897-12911	3.8	12
735	Evolution of the mechanical properties of Ti-based intermetallic thin films doped with different metals to be used as biomedical devices. *Applied Surface Science*, **2020**, 505, 144617	6.7	6

734	Deuterium inventory determination in beryllium and mixed beryllium-carbon layers doped with oxygen. *Fusion Engineering and Design*, **2020**, 150, 111365	1.7	3
733	Ion beam analysis of fusion plasma-facing materials and components: facilities and research challenges. *Nuclear Fusion*, **2020**, 60, 025001	3.3	28
732	Estimating the uncertainties of strain and damage analysis by X-ray diffraction in ion implanted MoO3. *Nuclear Instruments & Methods in Physics Research B*, **2020**, 478, 290-296	1.2	
731	Lithium dilution in Li-Sn alloys. *Nuclear Materials and Energy*, **2020**, 25, 100783	2.1	1
730	Ion beam induced current analysis in GaN microwires. *EPJ Web of Conferences*, **2020**, 233, 05001	0.3	1
729	Thin films of Au-Al2O3 for plasmonic sensing. *Applied Surface Science*, **2020**, 500, 144035	6.7	7
728	Metallic filamentary conduction in valence change-based resistive switching devices: the case of TaO thin film with x~ 1. *Nanoscale*, **2019**, 11, 16978-16990	7.7	10
727	Overview of the JET preparation for deuterium–tritium operation with the ITER like-wall. *Nuclear Fusion*, **2019**, 59, 112021	3.3	55
726	Direct observation of mono-vacancy and self-interstitial recovery in tungsten. *APL Materials*, **2019**, 7, 021103	5.7	25
725	New WC-Cu composites for the divertor in fusion reactors. *Journal of Nuclear Materials*, **2019**, 521, 31-37	3.3	5
724	Measuring strain caused by ion implantation in GaN. *Materials Science in Semiconductor Processing*, **2019**, 98, 95-99	4.3	8
723	Luminescence properties of MOCVD grown Al0.2Ga0.8N layers implanted with Tb. *Journal of Luminescence*, **2019**, 210, 413-424	3.8	
722	Deposition of impurity metals during campaigns with the JET ITER-like Wall. *Nuclear Materials and Energy*, **2019**, 19, 218-224	2.1	14
721	Stability of beryllium coatings deposited on carbon under annealing up to 1073 K. *Fusion Engineering and Design*, **2019**, 146, 303-307	1.7	2
720	Thin films composed of metal nanoparticles (Au, Ag, Cu) dispersed in AlN: The influence of composition and thermal annealing on the structure and plasmonic response. *Thin Solid Films*, **2019**, 676, 12-25	2.2	9
719	The effect of increasing Si content in the absorber layers (CrAlSiNx/CrAlSiOyNx) of solar selective absorbers upon their selectivity and thermal stability. *Applied Surface Science*, **2019**, 481, 1096-1102	6.7	6
718	First mirror test in JET for ITER: Complete overview after three ILW campaigns. *Nuclear Materials and Energy*, **2019**, 19, 59-66	2.1	16
717	Tritium distributions on W-coated divertor tiles used in the third JET ITER-like wall campaign. *Nuclear Materials and Energy*, **2019**, 18, 258-261	2.1	8

716	Incorporation of Europium into GaN Nanowires by Ion Implantation. *Journal of Physical Chemistry C*, **2019**, 123, 11874-11887	3.8	7
715	Engineering strain and conductivity of MoO3 by ion implantation. *Acta Materialia*, **2019**, 169, 15-27	8.4	10
714	Deuterium retention on the tungsten-coated divertor tiles of JET ITER-like wall in 2015–2016 campaign. *Fusion Engineering and Design*, **2019**, 146, 1979-1982	1.7	5
713	Micro-Opto-Electro-Mechanical Device Based on Flexible β-Ga2O3 Micro-Lamellas. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3235-Q3241	2	0
712	Structural and optical studies of aluminosilicate films doped with (Tb3+, Er3+)/Yb3+ by ion implantation. *Nuclear Instruments & Methods in Physics Research B*, **2019**, 459, 71-75	1.2	2
711	Monte Carlo simulations of ion channeling in crystals containing dislocations and randomly displaced atoms. *Journal of Applied Physics*, **2019**, 126, 195107	2.5	11
710	Optical and photoconductive properties of indium sulfide fluoride thin films. *Thin Solid Films*, **2019**, 671, 49-52	2.2	5
709	Influence of Al/Si atomic ratio on optical and electrical properties of magnetron sputtered Al1-xSixOy coatings. *Thin Solid Films*, **2019**, 669, 475-481	2.2	3
708	Analysis of deposited layers with deuterium and impurity elements on samples from the divertor of JET with ITER-like wall. *Journal of Nuclear Materials*, **2019**, 516, 202-213	3.3	8
707	Analysis of the outer divertor hot spot activity in the protection video camera recordings at JET. *Fusion Engineering and Design*, **2019**, 139, 115-123	1.7	3
706	Deposition temperature influence on the wear behaviour of carbon-based coatings deposited on hardened steel. *Applied Surface Science*, **2019**, 475, 762-773	6.7	7
705	Compositional analysis by RBS, XPS and EDX of ZnO:Al,Bi and ZnO:Ga,Bi thin films deposited by d.c. magnetron sputtering. *Vacuum*, **2019**, 161, 268-275	3.7	10
704	Improved neutron activation dosimetry for fusion. *Fusion Engineering and Design*, **2019**, 139, 109-114	1.7	6
703	RBS/C, XRR, and XRD Studies of Damage Buildup in Er-Implanted ZnO. *Physica Status Solidi (B): Basic Research*, **2019**, 256, 1800364	1.3	13
702	CrAlSiN barrier layer to improve the thermal stability of W/CrAlSiNx/CrAlSiOyNx/SiAlOx solar thermal absorber. *Solar Energy Materials and Solar Cells*, **2019**, 191, 235-242	6.4	12
701	A study of solar thermal absorber stack based on CrAlSiNx/CrAlSiNxOy structure by ion beams. *Nuclear Instruments & Methods in Physics Research B*, **2019**, 450, 195-199	1.2	4
700	Measurement of proton induced γ-ray emission cross sections on Na from 1.0 to 4.1 MeV. *Nuclear Instruments & Methods in Physics Research B*, **2019**, 441, 108-118	1.2	6
699	Defect formation and optical activation of Tb implanted AlxGa1−xN films using channeled implantation at different temperatures. *Surface and Coatings Technology*, **2018**, 355, 29-39	4.4	5

698	Helium load on W-O coatings grown by pulsed laser deposition. *Surface and Coatings Technology*, **2018**, 355, 215-221	4.4	6
697	WC-Cu thermal barriers for fusion applications. *Surface and Coatings Technology*, **2018**, 355, 222-226	4.4	11
696	Thin films of Ag□Au nanoparticles dispersed in TiO2: influence of composition and microstructure on the LSPR and SERS responses. *Journal Physics D: Applied Physics*, **2018**, 51, 205102	3	18
695	Up-conversion emission of aluminosilicate and titania films doped with Er3+/Yb3+ by ion implantation and sol-gel solution doping. *Surface and Coatings Technology*, **2018**, 355, 162-168	4.4	9
694	Backscattering analysis of short period ZnO/MgO superlattices. *Surface and Coatings Technology*, **2018**, 355, 45-49	4.4	10
693	Optical investigations of europium ion implanted in nitride-based diode structures. *Surface and Coatings Technology*, **2018**, 355, 40-44	4.4	8
692	Crystal damage analysis of implanted AlxGa1-xN (0≤x≤1) by ion beam techniques. *Surface and Coatings Technology*, **2018**, 355, 55-60	4.4	8
691	Neutron spectroscopy measurements of 14 MeV neutrons at unprecedented energy resolution and implications for deuterium–tritium fusion plasma diagnostics. *Measurement Science and Technology*, **2018**, 29, 045502	2	20
690	A design of selective solar absorber for high temperature applications. *Solar Energy*, **2018**, 172, 177-183	6.8	26
689	Electrical characterization of molybdenum oxide lamellar crystals irradiated with UV light and proton beams. *Surface and Coatings Technology*, **2018**, 355, 50-54	4.4	4
688	Helium and deuterium irradiation effects in tungsten-based materials with titanium. *Surface and Coatings Technology*, **2018**, 355, 143-147	4.4	1
687	Radiation sensors based on GaN microwires. *Journal Physics D: Applied Physics*, **2018**, 51, 175105	3	6
686	Optimization of nanocomposite Au/TiO 2 thin films towards LSPR optical-sensing. *Applied Surface Science*, **2018**, 438, 74-83	6.7	40
685	Eu-Doped AlGaN/GaN Superlattice-Based Diode Structure for Red Lighting: Excitation Mechanisms and Active Sites. *ACS Applied Nano Materials*, **2018**, 1, 3845-3858	5.6	10
684	Thermal desorption spectrometry of beryllium plasma facing tiles exposed in the JET tokamak. *Fusion Engineering and Design*, **2018**, 133, 135-141	1.7	11
683	Zr-O-N coatings for decorative purposes: Study of the system stability by exploration of the deposition parameter space. *Surface and Coatings Technology*, **2018**, 343, 30-37	4.4	16
682	In-situ XRD vs ex-situ vacuum annealing of tantalum oxynitride thin films: Assessments on the structural evolution. *Applied Surface Science*, **2018**, 438, 14-19	6.7	1
681	New WC-Cu thermal barriers for fusion applications: High temperature mechanical behaviour. *Journal of Nuclear Materials*, **2018**, 498, 355-361	3.3	8

680	Analysis of retained deuterium on Be-based films: Ion implantation vs. in-situ loading. *Nuclear Materials and Energy*, **2018**, 17, 242-247	2.1	1
679	Deuterium retention and erosion in liquid Sn samples exposed to D2 and Ar plasmas in GyM device. *Nuclear Materials and Energy*, **2018**, 17, 253-258	2.1	9
678	Multiple optical centers in Eu-implanted AlN nanowires for solid-state lighting applications. *Applied Physics Letters*, **2018**, 113, 201905	3.4	6
677	CuxCrFeMoTi (x = 0.21, 0.44, 1) high entropy alloys as novel materials for fusion applications. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2018**, 238-239, 18-25	3.1	5
676	Thin films composed of Au nanoparticles embedded in AlN: Influence of metal concentration and thermal annealing on the LSPR band. *Vacuum*, **2018**, 157, 414-421	3.7	17
675	Ion irradiation-induced easy-cone anisotropy in double-MgO free layers for perpendicular magnetic tunnel junctions. *Applied Physics Letters*, **2018**, 112, 202403	3.4	11
674	In Situ Characterization and Modification of Ga2O3 Flakes Using an Ion Micro-Probe. *Physica Status Solidi (A) Applications and Materials Science*, **2018**, 215, 1800190	1.6	4
673	Assessment of erosion, deposition and fuel retention in the JET-ILW divertor from ion beam analysis data. *Nuclear Materials and Energy*, **2017**, 12, 559-563	2.1	23
672	Deuterium retention in tin (Sn) and lithium in (LiSn) samples exposed to ISTTOK plasmas. *Nuclear Materials and Energy*, **2017**, 12, 709-713	2.1	24
671	Behavior of liquid Li-Sn alloy as plasma facing material on ISTTOK. *Fusion Engineering and Design*, **2017**, 117, 208-211	1.7	14
670	Asymmetric ZnO/ZnMgO double quantum well structures grown on m-plane ZnO substrates by MBE. *Journal of Luminescence*, **2017**, 186, 262-267	3.8	9
669	Studies of lithium deposition and D retention on tungsten samples exposed to Li-seeded plasmas in PISCES-A. *Plasma Physics and Controlled Fusion*, **2017**, 59, 044006	2	4
668	Efficient temperature sensing using photoluminescence of Er/Yb implanted GaN thin films. *Sensors and Actuators B: Chemical*, **2017**, 248, 769-776	8.5	31
667	Validity of Vegard rule for Al1InxN (0.08 . *Journal Physics D: Applied Physics*, **2017**, 50, 205107	3	8
666	Thermal and chemical stability of the W2N nitride phase. *Nuclear Materials and Energy*, **2017**, 12, 462-467	2.1	8
665	SiGe layer thickness effect on the structural and optical properties of well-organized SiGe/SiO multilayers. *Nanotechnology*, **2017**, 28, 345701	3.4	5
664	Optical and structural analysis of solar selective absorbing coatings based on AlSiOx:W cermets. *Solar Energy*, **2017**, 150, 335-344	6.8	35
663	Helium and deuterium irradiation effects in W-Ta composites produced by pulse plasma compaction. *Journal of Nuclear Materials*, **2017**, 492, 105-112	3.3	7

662	Study of deuterium retention in Be-W coatings with distinct roughness profiles. *Fusion Engineering and Design*, **2017**, 124, 464-467	1.7	5
661	Overview of the JET ITER-like wall divertor. *Nuclear Materials and Energy*, **2017**, 12, 499-505	2.1	36
660	Effects of thermal annealing on the structural and electronic properties of rare earth-implanted MoO3 nanoplates. *CrystEngComm*, **2017**, 19, 2339-2348	3.3	3
659	Fuel inventory and deposition in castellated structures in JET-ILW. *Nuclear Fusion*, **2017**, 57, 066027	3.3	20
658	Formation of metastable phases in Zr-ion-irradiated Al2O3 upon thermal annealing. *Journal of Electron Microscopy*, **2017**, 66, 388-396		
657	Characterization of magnetron sputtered sub-stoichiometric CrAlSiN x and CrAlSiO y N x coatings. *Surface and Coatings Technology*, **2017**, 328, 134-141	4.4	12
656	Investigation and plasma cleaning of first mirrors coated with relevant ITER contaminants: beryllium and tungsten. *Nuclear Fusion*, **2017**, 57, 086019	3.3	13
655	Overview of the JET results in support to ITER. *Nuclear Fusion*, **2017**, 57, 102001	3.3	125
654	Overview of fuel inventory in JET with the ITER-like wall. *Nuclear Fusion*, **2017**, 57, 086045	3.3	35
653	Impurity re-distribution in the corner regions of the JET divertor. *Physica Scripta*, **2017**, T170, 014060	2.6	5
652	Experience on divertor fuel retention after two ITER-Like Wall campaigns. *Physica Scripta*, **2017**, T170, 014063	2.6	21
651	Doping Ga2O3with europium: influence of the implantation and annealing temperature. *Journal Physics D: Applied Physics*, **2017**, 50, 325101	3	20
650	Implantation damage formation in a-, c- and m-plane GaN. *Acta Materialia*, **2017**, 123, 177-187	8.4	54
649	Assessing material properties for fusion applications by ion beams. *Nuclear Instruments & Methods in Physics Research B*, **2017**, 409, 255-258	1.2	2
648	Time-resolved deposition in the remote region of the JET-ILW divertor: measurements and modelling. *Physica Scripta*, **2017**, T170, 014059	2.6	5
647	Plasma wall interaction studies within the EUROfusion consortium: progress on plasma-facing components development and qualification. *Nuclear Fusion*, **2017**, 57, 116041	3.3	50
646	Corrosion Behavior of Titanium Oxynitrided by Diffusion and Magnetron Sputtering Methods in Physiological Solution. *Materials Performance and Characterization*, **2017**, 6, 20160074	0.5	
645	Quantitative x-ray diffraction analysis of bimodal damage distributions in Tm implanted Al0.15Ga0.85N. *Journal Physics D: Applied Physics*, **2016**, 49, 135308	3	15

644	Electrical insulation properties of RF-sputtered LiPON layers towards electrochemical stability of lithium batteries. *Journal Physics D: Applied Physics*, **2016**, 49, 485301	3	6
643	Determination of 9 Be(p,p 0) 9 Be, 9 Be(p,d 0) 8 Be and 9 Be(p,□0) 6 Li cross sections at 150□in the energy range 0.5□.35 MeV. *Nuclear Instruments & Methods in Physics Research B*, **2016**, 371, 50-53	1.2	7
642	Anisotropy of electrical conductivity in dc due to intrinsic defect formation in □Al2O3 single crystal implanted with Mg ions. *Nuclear Instruments & Methods in Physics Research B*, **2016**, 379, 91-94	1.2	1
641	Analysis of the Tb3+ recombination in ion implanted Al Ga1□N (0□□) layers. *Journal of Luminescence*, **2016**, 178, 249-258	3.8	5
640	The role and application of ion beam analysis for studies of plasma-facing components in controlled fusion devices. *Nuclear Instruments & Methods in Physics Research B*, **2016**, 371, 4-11	1.2	14
639	Study of nuclear reactions producing36Cl by micro-AMS. *Journal of Physics: Conference Series*, **2016**, 665, 012077	0.3	1
638	Magnetoelectric effect probe through ppm Fe doping in BaTiO3. *Journal of Alloys and Compounds*, **2016**, 661, 495-500	5.7	4
637	Functional behaviour of TiO2 films doped with noble metals. *Surface Engineering*, **2016**, 32, 554-561	2.6	12
636	Deposition in the inner and outer corners of the JET divertor with carbon wall and metallic ITER-like wall. *Physica Scripta*, **2016**, T167, 014052	2.6	9
635	Study of damage formation and annealing of implanted III-nitride semiconductors for optoelectronic devices. *Nuclear Instruments & Methods in Physics Research B*, **2016**, 379, 251-254	1.2	16
634	Electrochemical characterization of nanostructured Ag:TiN thin films produced by glancing angle deposition on polyurethane substrates for bio-electrode applications. *Journal of Electroanalytical Chemistry*, **2016**, 768, 110-120	4.1	9
633	Long-term fuel retention in JET ITER-like wall. *Physica Scripta*, **2016**, T167, 014075	2.6	44
632	Mechanisms of Implantation Damage Formation in AlxGa1□N Compounds. *Journal of Physical Chemistry C*, **2016**, 120, 7277-7283	3.8	30
631	Quantum well intermixing and radiation effects in InGaN/GaN multi quantum wells **2016**,		1
630	Raman microscopy investigation of beryllium materials. *Physica Scripta*, **2016**, T167, 014027	2.6	8
629	Study of In distribution on GaInSb:Al crystals by ion beam techniques. *Nuclear Instruments & Methods in Physics Research B*, **2016**, 371, 278-282	1.2	3
628	Effect of AlN content on the lattice site location of terbium ions in AlxGa1□N compounds. *Semiconductor Science and Technology*, **2016**, 31, 035026	1.8	10
627	Nanoscale triboactivity of functionalized c-Si surfaces by Fe+ ion implantation. *Journal of Physics Condensed Matter*, **2016**, 28, 134003	1.8	1

626	Ag:TiN-Coated Polyurethane for Dry Biopotential Electrodes: From Polymer Plasma Interface Activation to the First EEG Measurements. *Plasma Processes and Polymers*, **2016**, 13, 341-354	3.4	17
625	Impact of implantation geometry and fluence on structural properties of AlxGa1-xN implanted with thulium. *Journal of Applied Physics*, **2016**, 120, 165703	2.5	7
624	High Orbital Angular Momentum Harmonic Generation. *Physical Review Letters*, **2016**, 117, 265001	7.4	46
623	Utilization of native oxygen in Eu(RE)-doped GaN for enabling device compatibility in optoelectronic applications. *Scientific Reports*, **2016**, 6, 18808	4.9	28
622	Identifying the influence of the intrinsic defects in Gd-doped ZnO thin-films. *Journal of Applied Physics*, **2016**, 119, 065301	2.5	38
621	Spectroscopic analysis of the NIR emission in Tm implanted AlxGa1-xN layers. *Journal of Applied Physics*, **2016**, 120, 081701	2.5	7
620	Correction to Spectroscopic Analysis of Eu3+ Implanted and Annealed GaN Layers and Nanowires *Journal of Physical Chemistry C*, **2016**, 120, 6907-6908	3.8	5
619	Composition measurement of epitaxial ScxGa1xN films. *Semiconductor Science and Technology*, **2016**, 31, 064002	1.8	3
618	Study of the electrical behavior of nanostructured TiAg thin films, prepared by Glancing Angle Deposition. *Materials Letters*, **2015**, 157, 188-192	3.3	9
617	Corundum-to-spinel structural phase transformation in alumina. *Nuclear Instruments & Methods in Physics Research B*, **2015**, 358, 136-141	1.2	11
616	Biological behaviour of thin films consisting of Au nanoparticles dispersed in a TiO2 dielectric matrix. *Vacuum*, **2015**, 122, 360-368	3.7	18
615	Spectroscopic Analysis of Eu3+ Implanted and Annealed GaN Layers and Nanowires. *Journal of Physical Chemistry C*, **2015**, 119, 17954-17964	3.8	12
614	Ag y :TiN x thin films for dry biopotential electrodes: the effect of composition and structural changes on the electrical and mechanical behaviours. *Applied Physics A: Materials Science and Processing*, **2015**, 119, 169-178	2.6	2
613	Composition, structure and morphology of Al1InxN thin films grown on Al1GayN templates with different GaN contents. *Journal Physics D: Applied Physics*, **2015**, 48, 015103	3	4
612	Peculiar Magnetoelectric Coupling in BaTiOFeppm Nanoscopic Segregations. *ACS Applied Materials & Interfaces*, **2015**, 7, 24741-7	9.5	9
611	Structure dependent resistivity and dielectric characteristics of tantalum oxynitride thin films produced by magnetron sputtering. *Applied Surface Science*, **2015**, 354, 298-305	6.7	12
610	Retention behaviour of deuterium and helium in beryllium under single D+ and dual He+/D+ exposure. *Fusion Engineering and Design*, **2015**, 98-99, 1362-1366	1.7	3
609	Composition and structure variation for magnetron sputtered tantalum oxynitride thin films, as function of deposition parameters. *Applied Surface Science*, **2015**, 358, 508-517	6.7	5

608	Global erosion and deposition patterns in JET with the ITER-like wall. *Journal of Nuclear Materials*, **2015**, 463, 157-161	3.3	42
607	Consolidation of W□Ta composites: Hot isostatic pressing and spark and pulse plasma sintering. *Fusion Engineering and Design*, **2015**, 98-99, 1950-1955	1.7	25
606	Optical properties of zirconium oxynitride films: The effect of composition, electronic and crystalline structures. *Applied Surface Science*, **2015**, 358, 660-669	6.7	14
605	Optical performance of thin films produced by the pulsed laser deposition of SiAlON and Er targets. *Applied Surface Science*, **2015**, 336, 274-277	6.7	5
604	Evolution of the functional properties of titanium□silver thin films for biomedical applications: Influence of in-vacuum annealing. *Surface and Coatings Technology*, **2015**, 261, 262-271	4.4	15
603	Quantitative Chemical Mapping of InGaN Quantum Wells from Calibrated High-Angle Annular Dark Field Micrographs. *Microscopy and Microanalysis*, **2015**, 21, 994-1005	0.5	3
602	Growth of mixed materials in the Be/W/O system in fusion devices. *Microscopy and Microanalysis*, **2015**, 21, 94-95	0.5	
601	W-Ta Composites Consolidated by Spark Plasma Sintering. *Microscopy and Microanalysis*, **2015**, 21 Suppl 5, 27-8	0.5	
600	Luminescence studies on green emitting InGaN/GaN MQWs implanted with nitrogen. *Scientific Reports*, **2015**, 5, 9703	4.9	18
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